



62mm C-Serien Modul mit schnellem Trench/Feldstopp IGBT4 und optimierter Emitter Controlled Diode
62mm C-series module with fast trench/fieldstop IGBT4 and optimized Emitter Controlled diode

暫定データ
Preliminary Data

IGBT- インバータ / IGBT, Inverter
最大定格 / Maximum Rated Values

コレクタ・エミッタ間電圧 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
連続DCコレクタ電流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	200 320	A A
繰り返しピークコレクタ電流 Repetitive peak collector current	$t_P = 1\text{ms}$	I_{CRM}	400	A
トータル損失 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	1100	W
ゲート・エミッタ間ピーク電圧 Gate-emitter peak voltage		V_{GES}	+/-20	V

電気的特性 / Characteristic Values

			min.	typ.	max.		
コレクタ・エミッタ間飽和電圧 Collector-emitter saturation voltage	$I_C = 200\text{A}, V_{GE} = 15\text{V}$ $I_C = 200\text{A}, V_{GE} = 15\text{V}$ $I_C = 200\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,75 2,05 2,10	2,15	V V V	
ゲート・エミッタ間しきい値電圧 Gate threshold voltage	$I_C = 7,60\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4	V
ゲート電荷量 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		Q_G	1,80			μC
内蔵ゲート抵抗 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	3,8			Ω
入力容量 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{ies}	14,0			nF
帰還容量 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{res}	0,50			nF
コレクタ・エミッタ間遮断電流 Collector-emitter cut-off current	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			5,0	mA
ゲート・エミッタ間漏れ電流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
ターンオン遅れ時間 (誘導負荷) Turn-on delay time, inductive load	$I_C = 200\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 2,4\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,16 0,17 0,18			μs μs μs
ターンオン上昇時間 (誘導負荷) Rise time, inductive load	$I_C = 200\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 2,4\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,04 0,045 0,50			μs μs μs
ターンオフ遅れ時間 (誘導負荷) Turn-off delay time, inductive load	$I_C = 200\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 2,4\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,45 0,52 0,54			μs μs μs
ターンオフ下降時間 (誘導負荷) Fall time, inductive load	$I_C = 200\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 2,4\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,10 0,16 0,16			μs μs μs
ターンオンスイッチング損失 Turn-on energy loss per pulse	$I_C = 200\text{A}, V_{CE} = 600\text{V}, L_S = 30\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 4000\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 2,4\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	10,0 15,0 17,0			mJ mJ mJ
ターンオフスイッチング損失 Turn-off energy loss per pulse	$I_C = 200\text{A}, V_{CE} = 600\text{V}, L_S = 30\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 4500\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 2,4\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	14,0 20,0 23,0			mJ mJ mJ
短絡電流 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 900\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	800			A
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	IGBT部 (1素子当り) / per IGBT		R_{thJC}			0,135	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	IGBT部 (1素子当り) / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,034			K/W
動作温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

prepared by: MK	date of publication: 2013-11-04
approved by: WR	revision: 2.0



暫定データ
Preliminary Data

Diode、インバータ / Diode, Inverter
最大定格 / Maximum Rated Values

ピーク繰返し逆電圧 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
連続DC電流 Continuous DC forward current		I_F	200	A
ピーク繰返し順電流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	400	A
電流二乗時間積 I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	7800 7400	A ² s A ² s

電気的特性 / Characteristic Values

			min.	typ.	max.	
順電圧 Forward voltage	$I_F = 200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,65 1,65 1,65	2,15	V V V
ピーク逆回復電流 Peak reverse recovery current	$I_F = 200\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	230 250 260		A A A
逆回復電荷量 Recovered charge	$I_F = 200\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	20,0 32,0 45,0		μC μC μC
逆回復損失 Reverse recovery energy	$I_F = 200\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	9,00 16,0 17,5		mJ mJ mJ
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	/Diode (1 素子当り) / per diode		R_{thJC}		0,20	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	/Diode (1 素子当り) / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,05		K/W
動作温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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モジュール / Module

絶縁耐圧 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	4,0		kV
ベースプレート材質 Material of module baseplate			Cu		
内部絶縁 Internal isolation	基礎絶縁 (クラス1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
沿面距離 Creepage distance	連絡方法 - ヒートシンク / terminal to heatsink 連絡方法 - 連絡方法 / terminal to terminal		29,0 23,0		mm
空間距離 Clearance	連絡方法 - ヒートシンク / terminal to heatsink 連絡方法 - 連絡方法 / terminal to terminal		23,0 11,0		mm
相対トラッキング指数 Comperative tracking index		CTI	> 400		
			min. typ. max.		
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	/モジュール / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}	0,01		K/W
内部インダクタンス Stray inductance module		L _{sCE}	20		nH
パワーターミナル・チップ間抵抗 Module lead resistance, terminals - chip	T _C = 25°C, /スイッチ / per switch	R _{CC+EE'}	0,70		mΩ
保存温度 Storage temperature		T _{stg}	-40	125	°C
取り付けネジ締め付けトルク Mounting torque for modul mounting	取り付けネジ M6 適切なアプリケーションノートによるマウンティング Screw M6 - Mounting according to valid application note	M	3,00	-	6,00 Nm
主端子ネジ締め付けトルク Terminal connection torque	取り付けネジ M6 適切なアプリケーションノートによるマウンティング Screw M6 - Mounting according to valid application note	M	2,5	-	5,0 Nm
質量 Weight		G	340		g

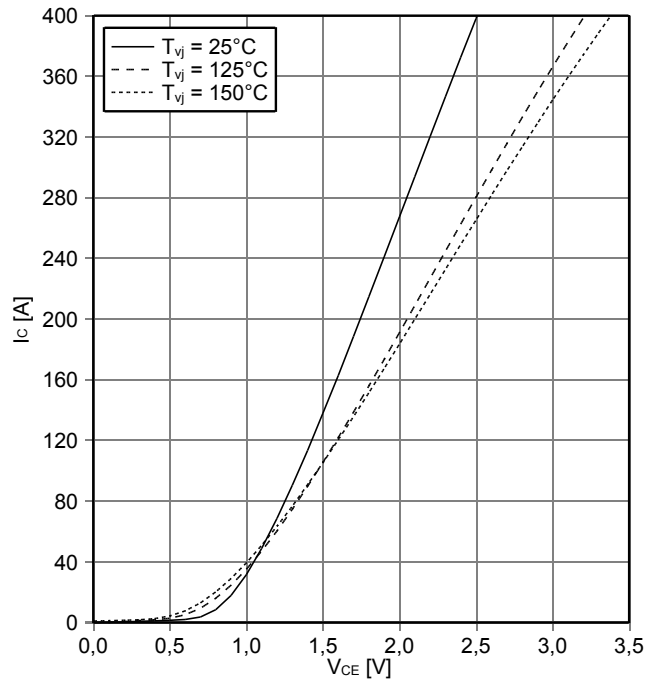
prepared by: MK	date of publication: 2013-11-04
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Preliminary Data

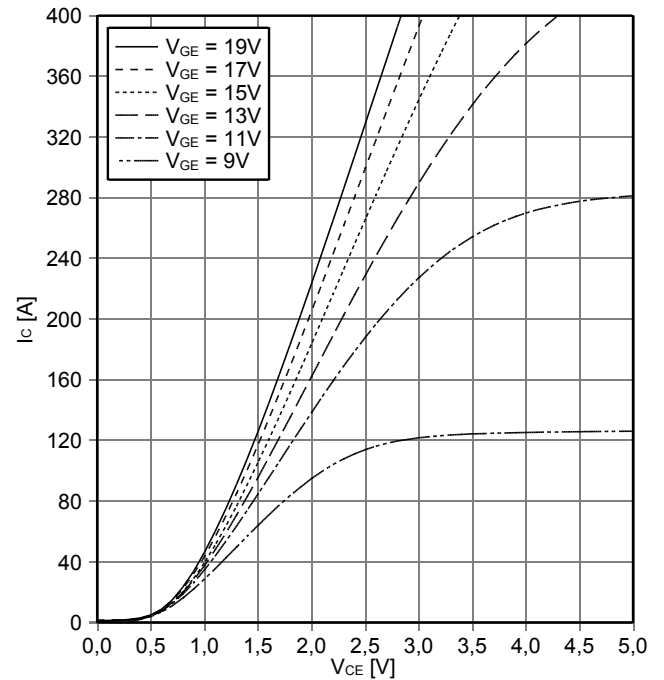
出力特性 IGBT- インバータ (Typical)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



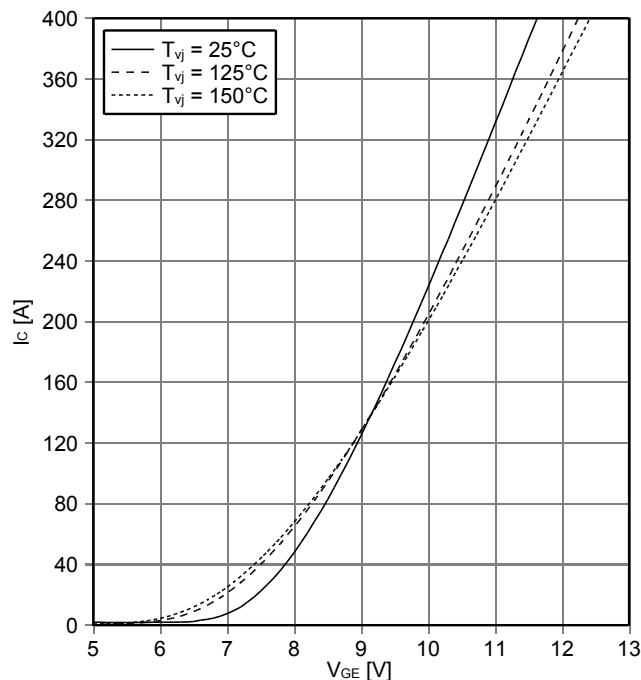
出力特性 IGBT- インバータ (Typical)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



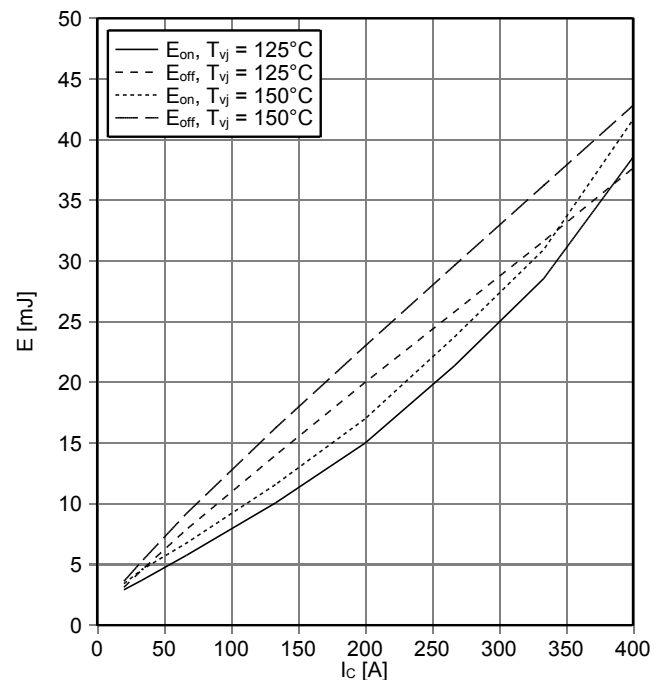
伝達特性 IGBT- インバータ (Typical)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



スイッチング損失 IGBT- インバータ (Typical)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 2.4\ \Omega$, $R_{Goff} = 2.4\ \Omega$, $V_{CE} = 600\text{ V}$



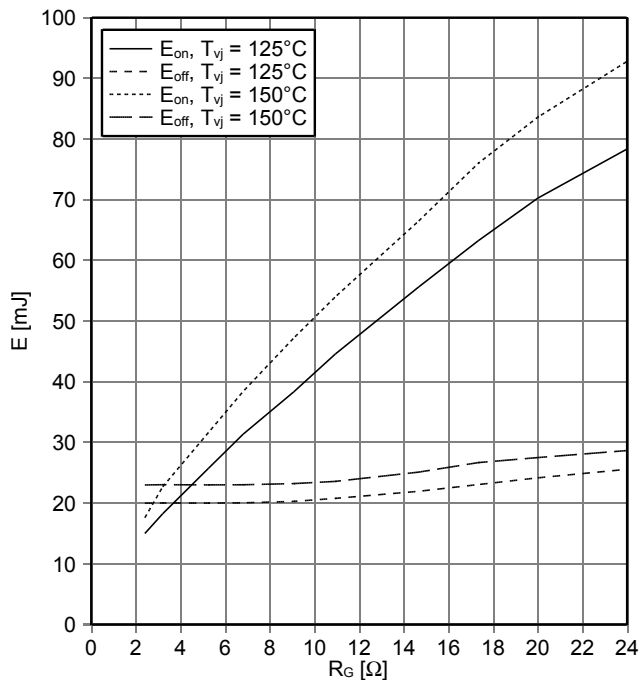
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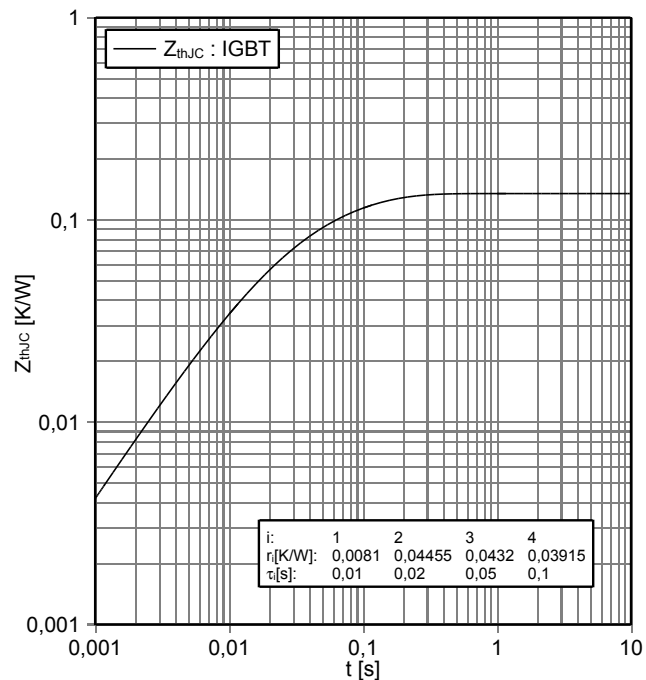
スイッチング損失 IGBT- インバータ (Typical)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 200\text{ A}, V_{CE} = 600\text{ V}$



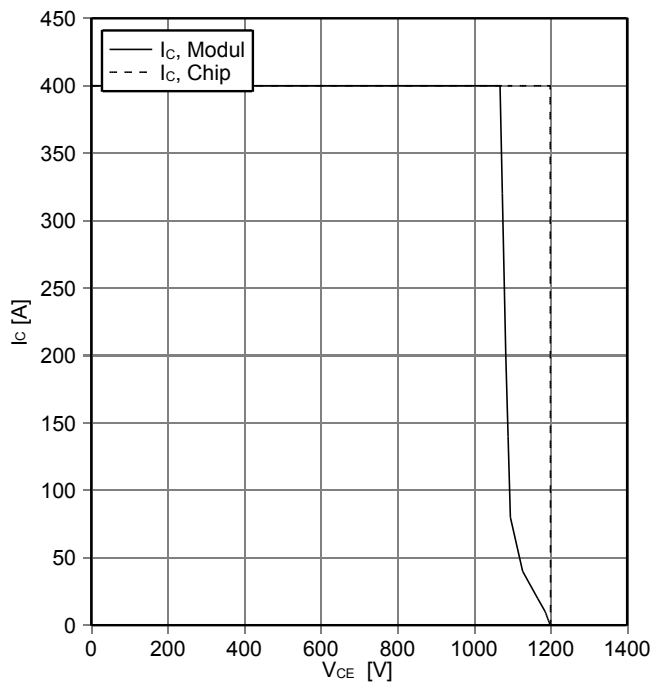
過渡熱インピーダンス IGBT- インバータ
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



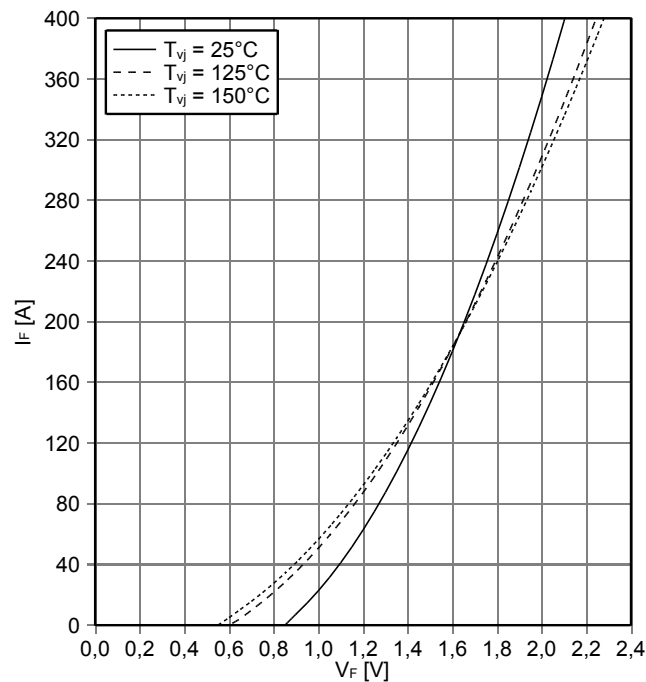
逆バイアス安全動作領域 IGBT- インバータ (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 2.4\ \Omega, T_{vj} = 150^\circ\text{C}$



順電圧特性 Diode、インバータ (typical)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



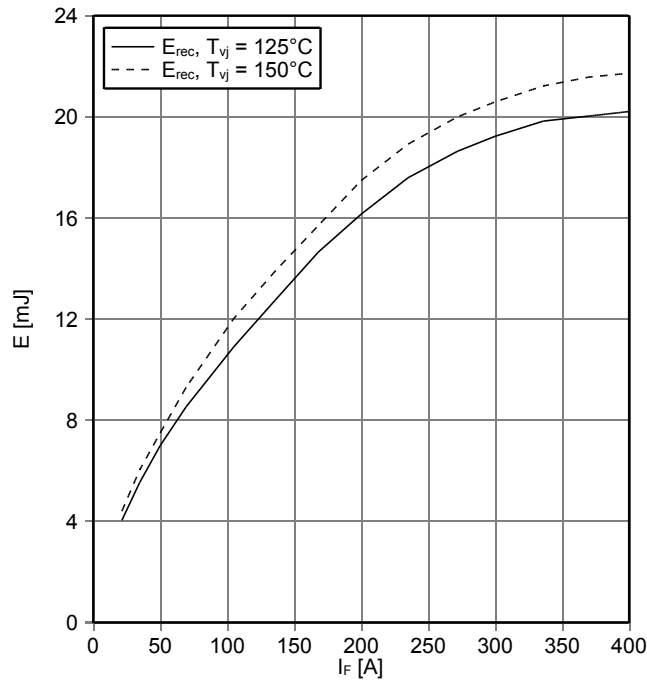
prepared by: MK	date of publication: 2013-11-04
approved by: WR	revision: 2.0



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Preliminary Data

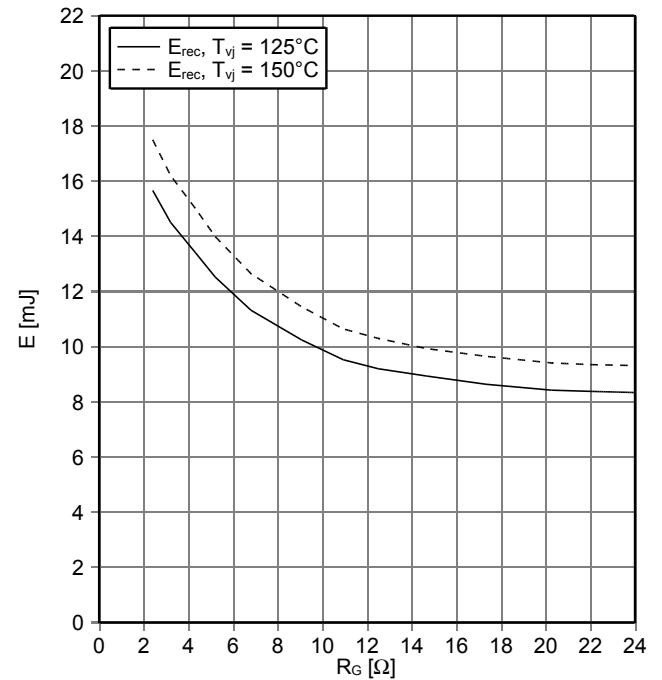
スイッチング損失 Diode、インバータ (Typical)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 2.4 \Omega, V_{CE} = 600 V$



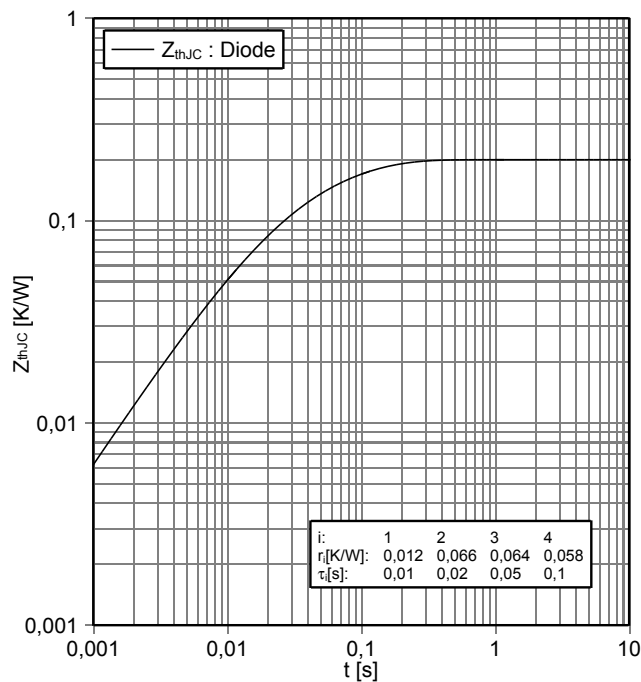
スイッチング損失 Diode、インバータ (Typical)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 200 A, V_{CE} = 600 V$



過渡熱インピーダンス Diode、インバータ
transient thermal impedance Diode, Inverter

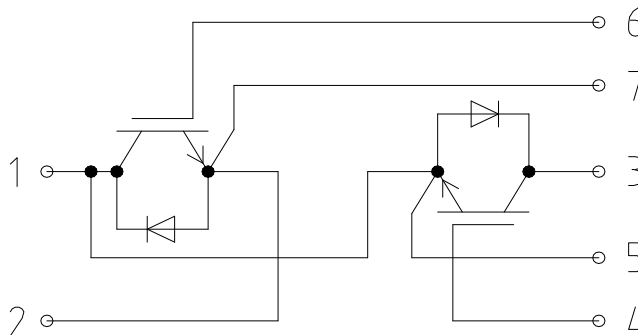
$Z_{thJC} = f(t)$



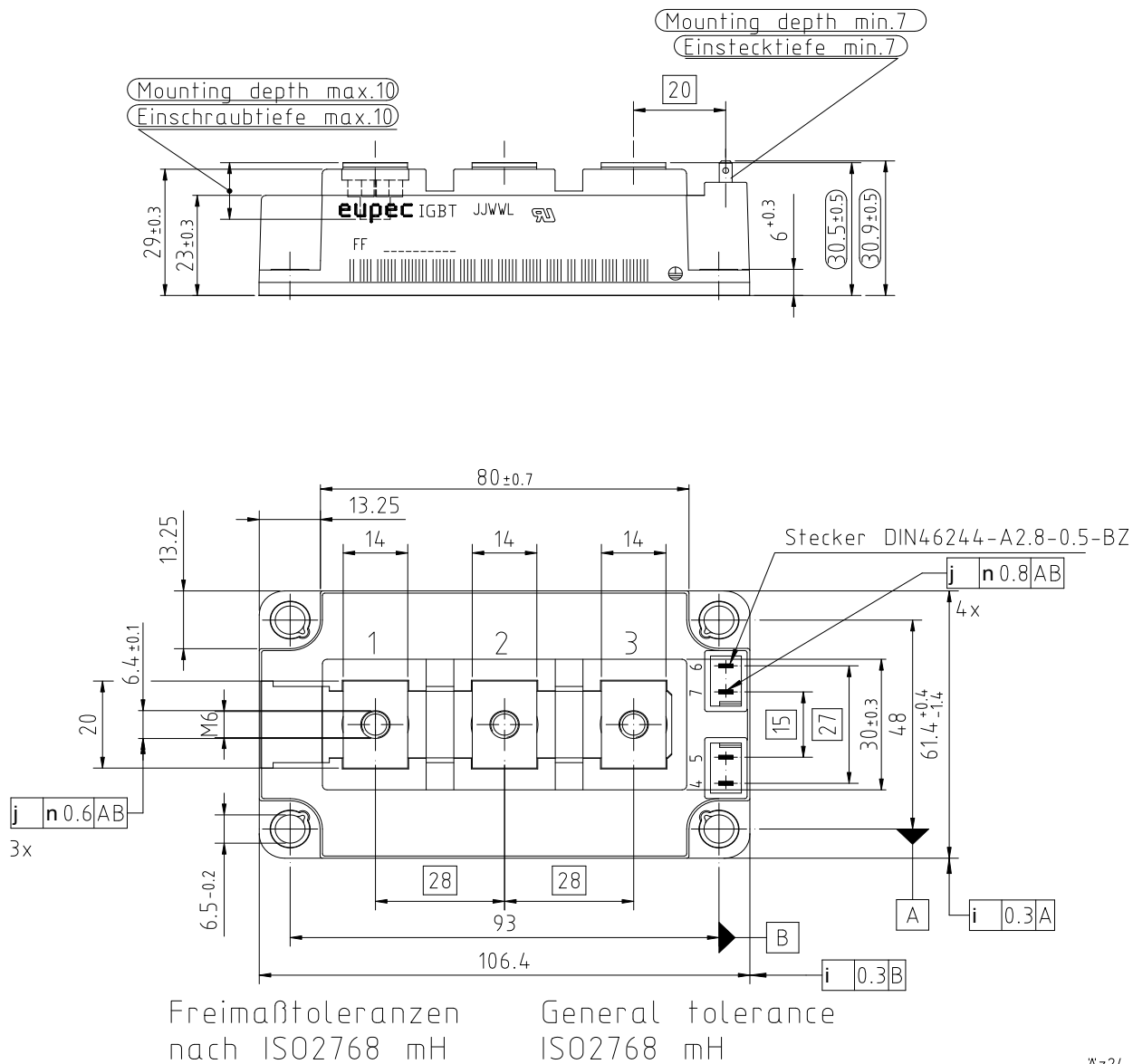
prepared by: MK	date of publication: 2013-11-04
approved by: WR	revision: 2.0

暫定データ
Preliminary Data

回路図 / circuit_diagram_headline



パッケージ概要 / package outlines



prepared by: MK	date of publication: 2013-11-04
approved by: WR	revision: 2.0